	Type	L #	Hits	Search T xt	DBs	Time Stamp
1	BRS	L16	1980152	substrate or wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:20
2	BRS	L17	6861	"pad oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:20
3	BRS	L18	1084	"pad nitride"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:21
4	BRS	L19	2630136	opening or trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:21
5	BRS	L20	1105	"doped silicate glass"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:21

	Typ	L #	Hits	Search T xt	DBs	Time Stamp
6	BRS	L21	177748	SiN or "silicon nitride"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:21
7	BRS	L22	18	16 and 17 and 18 and 19 and 20 and 21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:23
8	BRS	L23	1749	(deposit$6 or fill$6) near4 21 near8 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:24
9	BRS	L24	97237	DRAM or "dynamic random access memory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:24
10	BRS	L25	468	23 and 24	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 15:24

	Type	L #	Hits	Search T xt	DBs	Time Stamp
11	BRS	L26	168	25 and barrier	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/23 15:36
12	BRS	L27	168	26 and 21	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/06/23 15:36

	Typ	L #	Hits	Search T xt	DBs	Tim Stamp
1	BRS	L31	1980152	substrate or wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:00
2	BRS	L32	6861	"pad oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:00
3	BRS	L33	1084	"pad nitride"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:00
4	BRS	L34	2630136	opening or trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:00
5	BRS	L35	1105	"doped silicate glass"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01

	Type	L #	Hits	S arch T xt	DBs	Tim Stamp
6	BRS	L36	177748	SiN or "silicon nitride"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
7	BRS	L38	1749	(deposit$6 or fill$6) near4 (SiN or "silicon nitride") near8 (opening or trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
8	BRS	L39	97237	DRAM or "dynamic random access memory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
9	BRS	L40	468	((deposit$6 or fill$6) near4 (SiN or "silicon nitride") near8 (opening or trench)) and (DRAM or "dynamic random access memory")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
10	BRS	L37	18	(substrate or wafer) and "pad oxide" and "pad nitride" and (opening or trench) and "doped silicate glass" and (SiN or "silicon nitride")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01

	Typ	L #	Hits	S arch Text	DBs	Time Stamp
11	BRS	L41	168	(((deposit$6 or fill$6) near4 (SiN or "silicon nitride") near8 (opening or trench)) and (DRAM or "dynamic random access memory")) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
12	BRS	L42	168	((((deposit$6 or fill$6) near4 (SiN or "silicon nitride") near8 (opening or trench)) and (DRAM or "dynamic random access memory")) and barrier) and (SiN or "silicon nitride")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
13	BRS	L43	100	trench adj capacitor and doped adj glass and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:01
14	IS&R	L44	2	("6316310").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06
15	IS&R	L45	110	(438/249).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06

	Typ	L #	Hits	S arch T xt	DBs	Time Stamp
16	IS&R	L49	88	(438/561).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:49
17	IS&R	L51	84	(438/392).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 19:22